the first conductivity type is a p-type conductor; and the second conductivity type is a n-type conductor.

- 8. (Amended) The semiconductor device of claim 5, wherein, the first conductivity type is a n-type conductor; and the second conductivity type is a p-type conductor.
- 9. (Amended) The method of claim 5, wherein a first conductive well area and a second conductive well area are separately formed within the deep well area.
- 10. (Amended) The method of claim 9, wherein the first conductive well area is formed of the first conductivity type; and the second conductive well area is formed of the second conductivity type.
- 11. (Amended) The method of claim 6, wherein the scribe lanes are formed at all portions surrounding the chip formation areas.
- 12. (Amended) The method of claim 6, further comprising removing the mask using plasma processing or plasma equipment.